

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6	fujitsu.as. and ando.in. and ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 11:52
L2	36	fujitsu.as. and ferroelectric near5 capacitor and transistor and substrate and length	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 11:58
L3	48	ferroelectric near5 capacitor and transistor and substrate and (length or distance) same side near5 capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 14:53
L4	1	"20050012125".pn. and bit adj line	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 12:26
L5	2	"20050012125".pn. and (bit adj line or bitline)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 13:30
L6	1	"20050087787".pn. and central	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 14:29
L7	0	ferroelectric near5 capacitor and transistor and substrate and (gate or word adj line) same (incline or inclined) same (longitudinal or lateral)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 13:55
L8	18	ferroelectric near5 capacitor and transistor and substrate and (gate or word adj line) same (incline or inclined)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 13:55
L9	1	"20050087787".pn. and orthogonal	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 14:30
L10	1	"20050087787".pn. and orthogonal and coincides	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 14:31
L11	226	ferroelectric near5 capacitor and transistor and substrate and orthogonal	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 14:53
L12	138	ferroelectric near5 capacitor and transistor and substrate and orthogonal near10 line	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 14:55

L13	10	ferroelectric near5 capacitor and transistor and substrate and orthogonal near10 line and line near5 connect near5 (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 15:19
L14	88	ferroelectric near5 capacitor and transistor and substrate and perpendicular near10 line same (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 15:21
L15	50	ferroelectric near5 capacitor and transistor and substrate and perpendicular near10 (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 15:21
L16	32	ferroelectric adj capacitor and transistor and substrate and perpendicular near10 (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 15:25
L17	193	ferroelectric adj capacitor and transistor and substrate and (perpendicular or orthogonal) same (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 15:33
L18	121	ferroelectric adj capacitor and transistor and substrate and (bitline or wordline or plateline or bit adj line or plate adj line or plate adj line) same (source or drain) same (perpendicular or orthogonal)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 15:35
L19	135	ferroelectric adj capacitor and transistor and substrate and (bitline or wordline or plateline or bit adj line or word adj line or plate adj line) same (source or drain) same (perpendicular or orthogonal)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 15:42
L20	139	ferroelectric adj capacitor and transistor and substrate and (bit adj line or bitline) near5 (perpendicular or orthogonal) near5 (word adj line or wordline or plate adj line or plateline)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 16:43
L21	7617	ferroelectric adj capacitor and transistor and substrate 257/295-300. ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/10 16:43